

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. <b>244824US2</b>		SERIAL NO. <b>10/698526</b> New Application	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT <b>Tamio IKEHASHI, et al.</b>			
				FILING DATE Herewith <b>11/3/03</b>		GROUP <b>2811</b>	
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
<i>a</i>	AA	5,355,330	10/11/94	Dai HISAMOTO, et al.			
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
<i>a</i>	AO	2002-246571	08/30/02	Japan (with English Abstract)			X
<i>a</i>	AP	2003-31693	01/31/03	Japan (with English Abstract)			X
<i>a</i>	AQ	5-347419	12/27/93	Japan (with English Abstract)			X
	AR						
	AS						
	AT						
	AU						
	AV						
<b>OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)</b>							
<i>a</i>	AW	T. Ohsawa, et al., "Memory Design Using One Transistor Gain Cell on SOI", ISSCC DIGEST OF TECHNICAL PAPERS, ISSCC 2002/ SESSION 9/ DRAM AND FERROELECTRIC MEMORIES/9.1, Feb. 2002, pgs 152-153 and 454					
	AX						
	AY						
	AZ					<input type="checkbox"/> Additional References sheet(s) attached	
Examiner <i>agc</i>				Date Considered <b>8-19-04</b>			
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							